

Please insert, additionally, new claim 58, as follows:

58. A method for manufacturing a semiconductor integrated circuit device, comprising the steps of:
 - (a) forming a groove in a first insulating film formed on a semiconductor substrate;
 - (b) depositing a copper film on said first insulating film including the groove;
 - (c) removing said copper film from outside of said groove to bury said copper film in said groove;
 - (d) cleaning with a solution capable of removing a foreign matter or a contaminant metal from a surface of said first insulating film to remove said contaminant metal that remains on a surface of said first insulating film;
 - (e) forming a cap conductive film on said copper film in said groove by selective growth of the cap conductive film on said copper film buried in said groove; and
 - (f) cleaning the resultant semiconductor substrate with a solution capable of removing foreign matter or a contaminant metal.